

**THE CLAIMS:**

1. Cancelled.
2. Cancelled.
3. Cancelled.
4. (Currently amended) A semiconductor device as set forth in claim ~~[[3]]~~ 10, wherein said metal layer is formed of an element selected from the group consisting of titanium, molybdenum, chromium, cobalt, tantalum, niobium and zirconium.
5. (Currently amended) A semiconductor device as set forth in claim ~~[[3]]~~ 10 or claim 4, wherein said insulating film is amorphous.
6. (Currently amended) A semiconductor device as set forth in claim ~~[[3]]~~ 10 or claim 4, wherein said insulating film has a film density of 1.5 g/cm<sup>3</sup> or higher.
7. (Currently amended) A semiconductor device as set forth in claim ~~[[3]]~~ 10 or claim 4, wherein said insulating film contains oxygen having a concentration of 3 atomic% or less.

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com

8. (Currently amended) A semiconductor device as set forth in claim ~~[[3]]~~ 10 or claim 4, wherein said insulating film contains nitrogen having a concentration of 3 atomic% or less.

9. (Currently amended) A semiconductor device as set forth in claim ~~[[3]]~~ 10 or claim 4, wherein said insulating film contains boron having a concentration of from  $10^{-3}$  atomic% to 1 atomic%.

10. (Currently amended) A semiconductor device comprising:  
a substrate;  
an insulating film of a fluorine-contained carbon film formed on said substrate,  
wherein the surface of said insulating film is irradiated with hydrogen plasma;  
a wiring layer of copper formed on said insulating film; and  
an adhesion layer formed between said insulating film and said wiring layer, for  
preventing said wiring layer from being peeled off from said insulating film, wherein said  
adhesion layer includes

a metal layer of a metal ~~A semiconductor device as set forth in claim 3,~~  
~~wherein said metal layer is disposed adjacent said wiring layer, and~~  
a layer of a compound containing carbon and said metal ~~said layer of a~~  
~~compound is disposed adjacent said insulating film.~~

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